

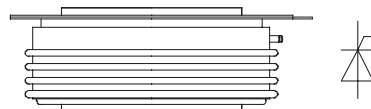
## FEATURES

- 1). Center amplifying gate
- 2). Metal case with ceramic insulator
- 3). Low on-state and switching losses

## TYPICAL APPLICATIONS

- 1). AC controllers
- 2). DC and AC motor control
- 3). Controlled rectifiers

$I_{T(AV)}$  1979A  
 $V_{DRM}/V_{RRM}$  400~1000V  
 $I_{TSM}$  30 KA  
 $I^2t$  4500 10<sup>3</sup>A<sup>2</sup>S



## THE MAIN PARAMETERS

SYMBOL	CHARACTERISTIC	TEST CONDITIONS		T <sub>J</sub> (℃)	VALUE			UNIT
					Min	Type	Max	
I <sub>T(AV)</sub>	Mean on-state current	180° half sine wave 50Hz Double side cooled,	T <sub>hs</sub> =55℃ T <sub>hs</sub> =68℃	125			1979 1600	A
V <sub>DRM</sub> V <sub>RRM</sub>	Repetitive peak off-state voltage Repetitive peak reverse voltage	V <sub>DRM</sub> &V <sub>RRM</sub> , tp=10ms V <sub>DSM</sub> &V <sub>RSM</sub> = V <sub>DRM</sub> &V <sub>RRM</sub> +100V		125	400		1000	V
I <sub>DRM</sub> I <sub>RRM</sub>	Repetitive peak off-state current Repetitive peak reverse current	V <sub>D</sub> = V <sub>DRM</sub> V <sub>R</sub> = V <sub>RRM</sub>		125			80	mA
I <sub>TSM</sub>	Surge on-state current	10ms half sine wave		125			30	KA
I <sup>2</sup> t	I <sup>2</sup> T for fusing coordination	V <sub>R</sub> =0.6V <sub>RRM</sub>		125			4500	A <sup>2</sup> s*10 <sup>3</sup>
V <sub>TO</sub>	Threshold voltage			125			0.89	V
r <sub>T</sub>	On-state slop resistance			125			0.12	mΩ
V <sub>TM</sub>	Peak on-state voltage	I <sub>TM</sub> =2550A, F=24KN		125			1.25	V
dv/dt	Critical rate of rise of off-state voltage	V <sub>DM</sub> =0.67V <sub>DRM</sub>		125			1000	V/ μ s
di/dt	Critical rate of rise of on-state current	V <sub>DM</sub> = 67%V <sub>DRM</sub> to2500A, Gate pulse t <sub>r</sub> ≤0.5 μ s I <sub>GM</sub> =1.5A		125			500	A/ μ s
I <sub>rm</sub>	Reverse recovery current	I <sub>TM</sub> =1500A,tp=1000 μ s, di/dt=-20A/ μ s, VR=50V		125			150	A
t <sub>rr</sub>	Reverse recovery time						20	μ s
Q <sub>rr</sub>	Recovery charge						1500	μ C
I <sub>GT</sub>	Gate trigger current	V <sub>A</sub> =12V, I <sub>A</sub> =1A		25	40		300	mA
V <sub>GT</sub>	Gate trigger voltage				0.8		3.0	V
I <sub>H</sub>	Holding current				20		300	mA
V <sub>GD</sub>	Non-trigger gate voltage	V <sub>DM</sub> =0.67V <sub>DRM</sub>		125	0.3			V
R <sub>th(j-h)</sub>	Thermal resistance Junction to heatsink	At 180° sine, double side cooled Clamping force 24KN					0.024	℃ /W
F <sub>m</sub>	Mounting force				19		26	KN
T <sub>stg</sub>	Stored temperature				-40		140	℃
W <sub>t</sub>	Weight					470		g
Size	Package box size	160 × 145 × 65						mm

## PERFORMANCE CURVES FIGURE

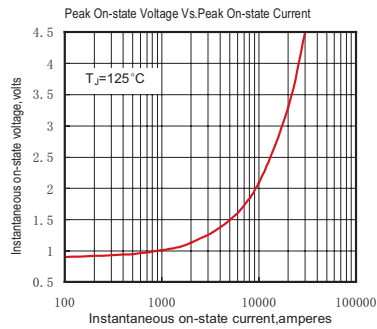


Fig.1

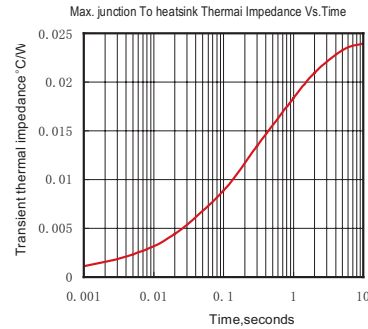


Fig.2

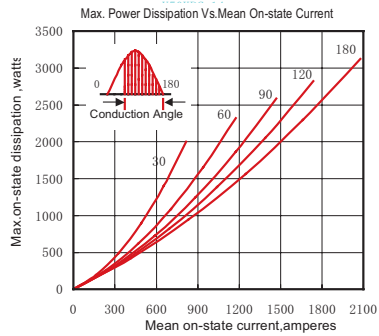


Fig.3

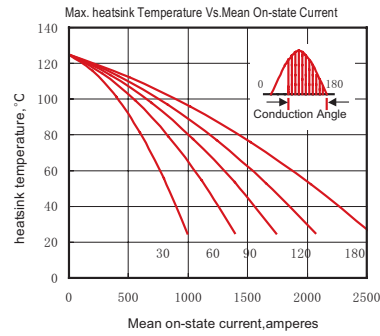


Fig.4

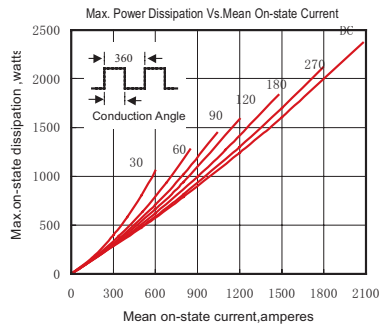


Fig.5

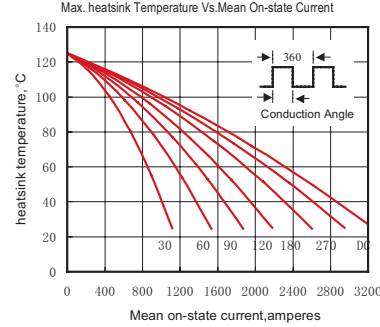


Fig.6

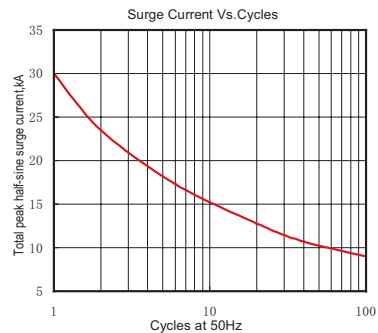


Fig.7

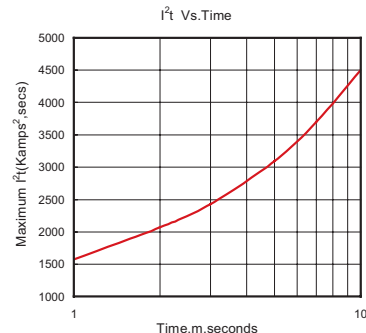


Fig.8

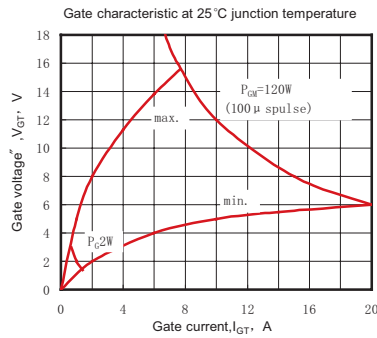


Fig.9

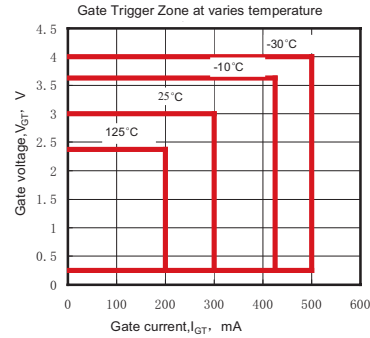
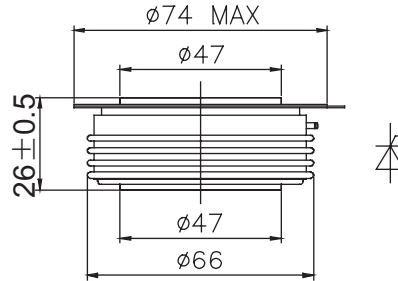
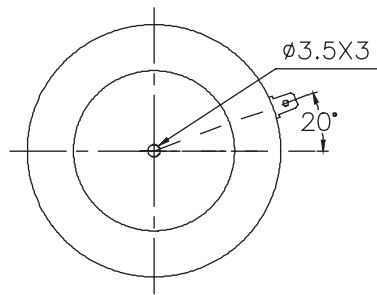


Fig.10

## OUTLINE



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